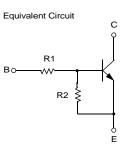


# **NPN Epitaxial Silicon Transistor**

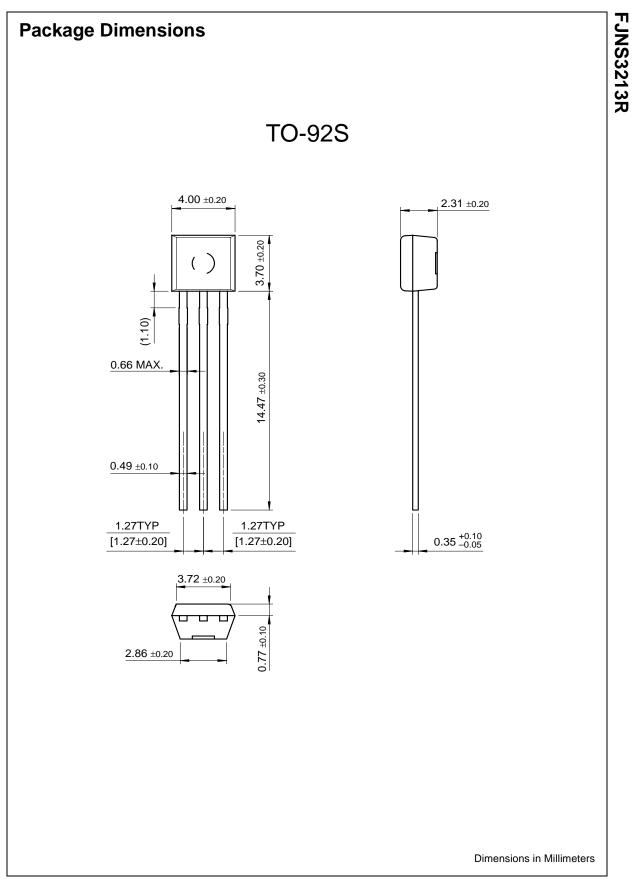
Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	10	V
I <sub>C</sub>	Collector Current	100	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C



# Electrical Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =10μA, I <sub>E</sub> =0	50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>B</sub> =0	50			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =5mA	68			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA			0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA		250		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0 f=1.0MHz		3.7		pF
V <sub>I</sub> (off)	Input Off Voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.5			V
V <sub>I</sub> (on)	Input On Voltage	V <sub>CE</sub> =0.2V, I <sub>C</sub> =5mA			1.1	V
R <sub>1</sub>	Input Resistor		1.5	2.2	2.9	KΩ
$R_1/R_2$	Resistor Ratio		0.042	0.047	0.052	



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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